

Title (en)  
SEMICONDUCTOR DIE HAVING A REDISTRIBUTION LAYER

Title (de)  
HALBLEITERCHIP MIT EINER UMVERDRAHTUNGSSCHICHT

Title (fr)  
DÉ SEMI-CONDUCTEUR DOTÉ D'UNE COUCHE DE REDISTRIBUTION

Publication  
**EP 2179442 A4 20130807 (EN)**

Application  
**EP 08796037 A 20080627**

Priority

- US 2008068542 W 20080627
- US 76992707 A 20070628
- US 76993707 A 20070628

Abstract (en)  
[origin: WO2009006284A2] A semiconductor device having a redistribution layer, and methods of forming same, are disclosed. After fabrication of semiconductor die on a wafer, a tape assembly is applied onto a surface of the wafer, in contact with the surfaces of each semiconductor die on the wafer. The tape assembly includes a backgrind tape as a base layer, and a film assembly adhered to the backgrind tape. The film assembly in turn includes an adhesive film on which is deposited a thin layer of conductive material. The redistribution layer pattern is traced into the tape assembly, using for example a laser. Thereafter, the unheated portions of the tape assembly may be removed, leaving the heated redistribution layer pattern on each semiconductor die.

IPC 8 full level  
**H01L 23/04** (2006.01); **H01L 21/683** (2006.01); **H01L 23/525** (2006.01)

CPC (source: EP)  
**H01L 21/6835** (2013.01); **H01L 21/6836** (2013.01); **H01L 23/3114** (2013.01); **H01L 23/525** (2013.01); **H01L 24/03** (2013.01); **H01L 24/48** (2013.01); **H01L 24/49** (2013.01); **H01L 2221/68327** (2013.01); **H01L 2221/68363** (2013.01); **H01L 2224/02313** (2013.01); **H01L 2224/02319** (2013.01); **H01L 2224/0401** (2013.01); **H01L 2224/05554** (2013.01); **H01L 2224/05599** (2013.01); **H01L 2224/11003** (2013.01); **H01L 2224/16** (2013.01); **H01L 2224/48091** (2013.01); **H01L 2224/48227** (2013.01); **H01L 2224/49175** (2013.01); **H01L 2224/85399** (2013.01); **H01L 2225/06562** (2013.01); **H01L 2924/00014** (2013.01); **H01L 2924/01005** (2013.01); **H01L 2924/01006** (2013.01); **H01L 2924/01013** (2013.01); **H01L 2924/01018** (2013.01); **H01L 2924/01022** (2013.01); **H01L 2924/01027** (2013.01); **H01L 2924/01033** (2013.01); **H01L 2924/01047** (2013.01); **H01L 2924/01078** (2013.01); **H01L 2924/01082** (2013.01); **H01L 2924/07802** (2013.01); **H01L 2924/10161** (2013.01); **H01L 2924/10162** (2013.01); **H01L 2924/14** (2013.01); **H01L 2924/1433** (2013.01); **H01L 2924/181** (2013.01)

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Designated contracting state (EPC)  
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MT NL NO PL PT RO SE SI SK TR

DOCDB simple family (publication)  
**WO 2009006284 A2 20090108; WO 2009006284 A3 20090409**; CN 101765911 A 20100630; CN 101765911 B 20120627; EP 2179442 A2 20100428; EP 2179442 A4 20130807; KR 101475467 B1 20141222; KR 20100034756 A 20100401; TW 200910474 A 20090301; TW I371807 B 20120901

DOCDB simple family (application)  
**US 2008068542 W 20080627**; CN 200880022454 A 20080627; EP 08796037 A 20080627; KR 20107001950 A 20080627; TW 97124363 A 20080627